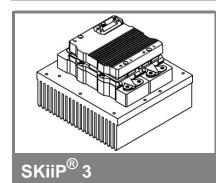
SKiiP 1213GB123-2DL



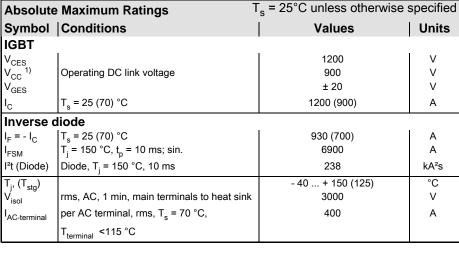
2-pack-integrated intelligent Power System

Power section SKiiP 1213GB123-2DL

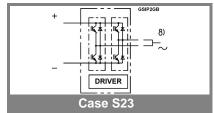
Data

Power section features

- · SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- · Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP[®] 3 System)
- IEC 60068-1 (climate) 40/125/56)
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal
- 8) AC connection busbars must be connected by the user; copper busbars available on request



Characteristics			T _s = 25°C unless otherwise specified					
Symbol	Conditions				min.	typ.	max.	Units
IGBT								
V _{CEsat}	I _C = 600 A measured at	., T _j = 25 (1 terminal	25) °C;			1,7 (1,9)	2,1	V
V_{CEO}		25) °C; at to				0,9 (0,8)	1,1 (1)	V
r _{CE}	T _j = 25 (125) °C; at terminal					1,3 (1,8)	1,7 (2,2)	mΩ
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES},$ $T_i = 25 (125) ^{\circ}C$					2,4 (72)		mA
E _{on} + E _{off}	I _C = 600 A, V _{CC} = 600 V					221		mJ
OII OII		C, V _{CC} = 9				390		mJ
R _{CC+EE}	terminal chip, T _i = 25 °C					mΩ		
L _{CE}	top, bottor	,			0,25 6			nΗ
C _{CHC}	per phase	, AC-side				3,4		nF
Inverse o	diode							
$V_F = V_{EC}$	I _F = 600 A measured at	., T _j = 25 (1 terminal	25) °C			1,5 (1,5)	1,8	V
V _{TO}	T _i = 25 (12	25) °C				0,9 (0,7)	1,1 (0,9)	V
r _T	$T_i = 25 (12)$					1 (1,3)	1,1 (1,5)	mΩ
Ė _{rr}	I _C = 600 A	, V _{CC} = 60	0 V			42		mJ
	T _j = 125 °	C, V _{CC} = 9	00 V			56		mJ
Mechani	cal data							
M_{dc}	DC terminals, SI Units			6		8	Nm	
M_{ac}	AC terminals, SI Units			13		15	Nm	
W	SKiiP® 3 System w/o heat sink					1,7		kg
W	heat sink					5,4		kg
							230-1); "s	
reference 60747-15		sınk; "r	" retere	nce to b	uilt-in ter	nperature	e sensor (acc. IEC
$R_{th(j-s)l}$	per IGBT				ĺ		0,03	K/W
R _{th(j-s)D}	per diode						0,058	K/W
Z _{th}	R _i (mK/W) (max. values)				tau _i (s)			
	1	2	3	4	1	2	3	4
$Z_{th(j-r)I}$	9,8	16,4	3,8	0	0,37	0,06	0,01	1
$Z_{\text{th(j-r)D}}$	10	24	24	36	50	5	0,25	0,04
$Z_{th(r-a)}$	4,3	20,3	7,1	2,3	160	53	9	0,4

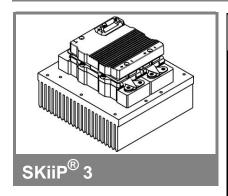


^{*} The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of

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2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1213GB123-2DL

Data

Gate driver features

- · CMOS compatible inputs
- · Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and
 - DC-bus voltage (option)
- · Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute	Maximum Ratings	a = 25°C unless otherwise specified		
Symbol	Conditions	Values	Units	
V_{S2}	unstabilized 24 V power supply	30	V	
V_{i}	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
V_{isollO}	input / output (AC, rms, 2s)	3000	V	
V _{isoIPD}	partial discharge extinction voltage, rms, Q _{PD} ≤10 pC;	1170	V	
V _{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V	
f _{sw}	switching frequency	15	kHz	
f _{out}	output frequency for I _{peak(1)} =I _C	15	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

Characte	ristics	(T _a = 25 °C)			
Symbol	Conditions	min.	typ.	max.	Units
V_{S2}	supply voltage non stabilized	13	24	30	V
I _{S2}	V _{S2} = 24 V	278+25*f/kHz+0,00022*(I _{AC} /A) ²			mA
V _{iT+}	input threshold voltage (High)			12,3	V
V_{iT-}	input threshold voltage (Low)	4,6			V
R _{IN}	input resistance		10		kΩ
C _{IN}	input capacitance		1		nF
$t_{d(on)IO}$	input-output turn-on propagation time		1,3		μs
t _{d(off)IO}	input-output turn-off propagation time		1,3		μs
t _{pERRRESET}	error memory reset time		9		μs
t_{TD}	top / bottom switch interlock time		3,3		μs
I _{analogOUT}	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		1200		Α
I _{s1out}	max. load current			50	mA
I _{TRIPSC}	over current trip level				
	(I _{analog} OUT = 10 V)		1500		Α
T _{tp}	over temperature protection	110		120	°C
U _{DCTRIP}	U _{DC} -protection (U _{analog OUT} = 9 V);	not implemented		d	V
	(option for GB types)				

For electrical and thermal design support please use SEMISEL.

Access to SEMISEL is via SEMIKRON website http://www.semikron.com.

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